

TNG50DN60DN

Dual N-Channel Enhancement Mode Power MOSFET

Product Summary

- $V_{DS} = 60V, I_D = 50A$
- $R_{DS(on)} = 6m\Omega @ V_{GS} = 10V$
- $R_{DS(on)} = 9m\Omega @ V_{GS} = 4.5V$

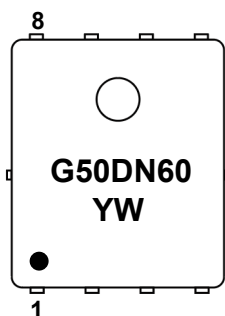
Features

- Advanced Trench Technology
- 100% Avalanche Tested
- RoHS Compliant
- Halogen and Antimony Free
- Moisture Sensitivity Level 3

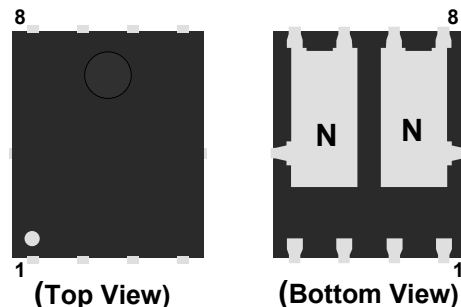
Application

- Synchronous Rectifiers
- H-bridge Motor Drive

Marking Code

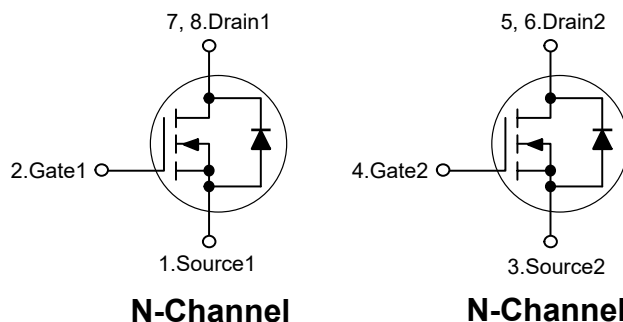


PDFN5x6A-8L



Pin	Description	Pin	Description
1	Source1	4	Gate2
2	Gate1	5,6	Drain2
3	Source2	7,8	Drain1

Schematic Diagram



Absolute Maximum Ratings

Ratings at 25°C case temperature unless otherwise specified.

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		60	V
V_{GSS}	Gate-Source Voltage		± 20	V
I_D	Continuous Drain Current	$T_C = 25^\circ C$	35	A
		$T_C = 100^\circ C$	26	A
I_{DM}	Pulsed Drain Current ^{note1}		180	A
E_{AS}	Single Pulsed Avalanche Energy ^{note2}		36	mJ
P_D	Power Dissipation	$T_C = 25^\circ C$	69	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		1.8	$^\circ C/W$
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +175	$^\circ C$

Electrical Characteristics

(T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	60	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =60V, V _{GS} =0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	-	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.6	2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance note3	V _{GS} =10V, I _D =20A	-	6	6.7	mΩ
		V _{GS} =4.5V, I _D =10A	-	9	12.1	
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1.0MHz	-	930	-	pF
C _{oss}	Output Capacitance		-	230	-	pF
C _{rss}	Reverse Transfer Capacitance		-	8	-	pF
Q _g	Total Gate Charge	V _{DS} =30V, I _D =20A, V _{GS} =10V	-	22	-	nC
Q _{gs}	Gate-Source Charge		-	4.5	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	3.5	-	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =30V, I _D =20A, R _G =1.6Ω, V _{GS} =10V	-	4.5	-	ns
t _r	Turn-on Rise Time		-	2.7	-	ns
t _{d(off)}	Turn-off Delay Time		-	13.8	-	ns
t _f	Turn-off Fall Time		-	2.7	-	ns
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	45	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	180	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =30A	-	-	1.2	V
t _{rr}	Body Diode Reverse Recovery Time	T _J =25℃, I _F =20A,dI/dt=100A/μs	-	18	-	ns
Q _{rr}	Body Diode Reverse Recovery Charge		-	12	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

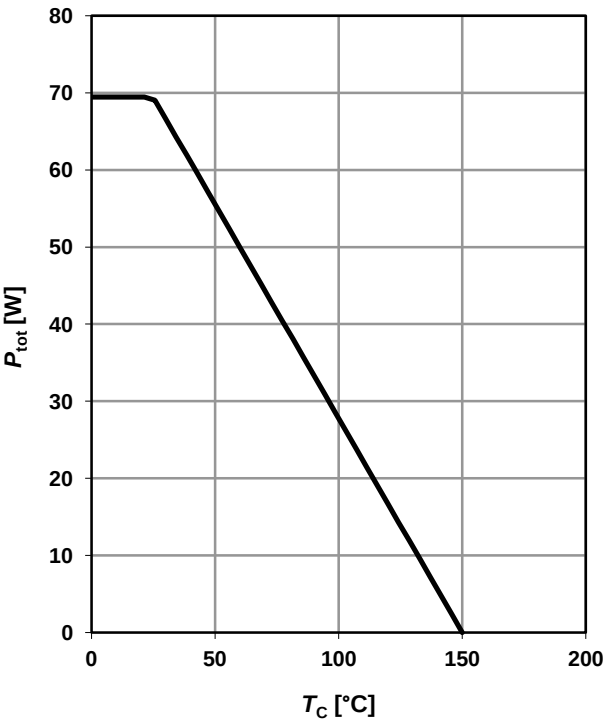
2. EAS condition: T_J=25°C, V_{DD}=30V, V_G=10V, R_G=25Ω, L=0.5mH, I_{AS}=12A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Typical Characteristic Curves

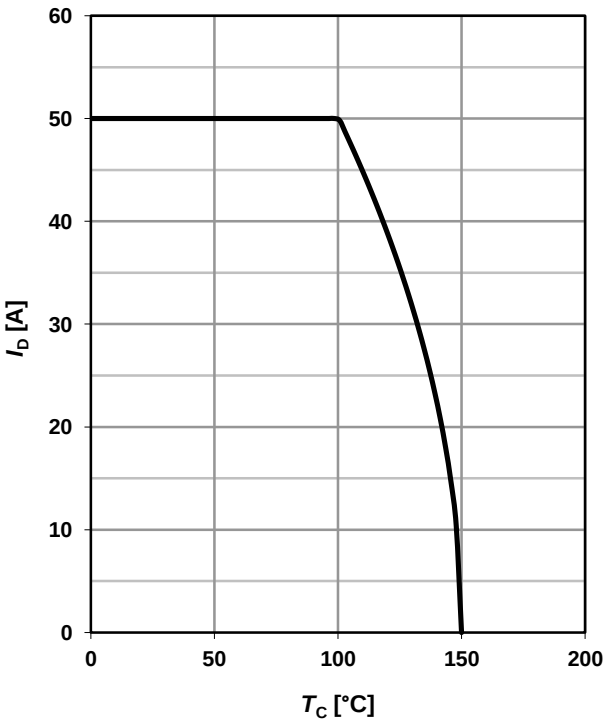
1 Power dissipation

$P_{tot}=f(T_C)$



2 Drain current

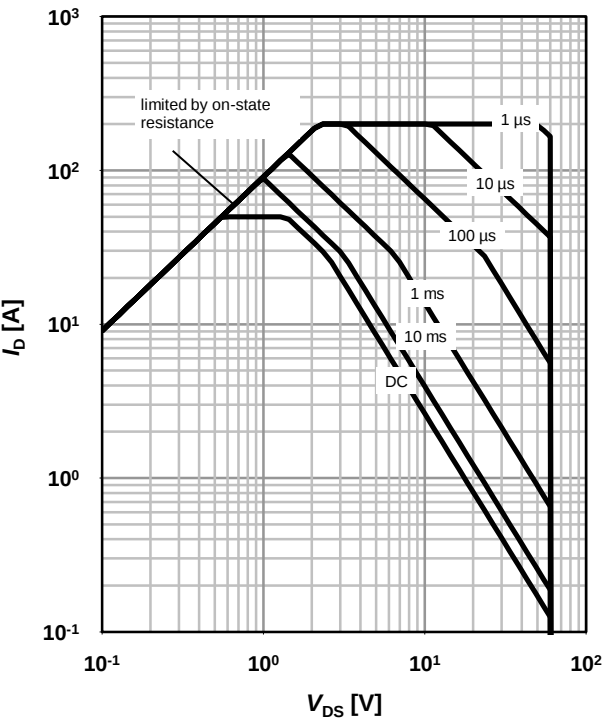
$I_D=f(T_C); V_{GS}\geq 10\text{ V}$



3 Safe operating area

$I_D=f(V_{DS}); T_C=25\text{ }^\circ\text{C}; D=0$

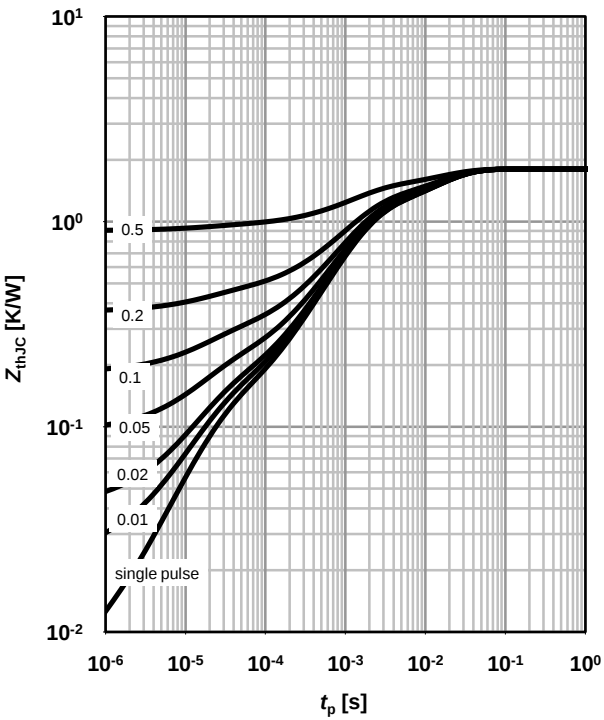
parameter: t_p



4 Max. transient thermal impedance

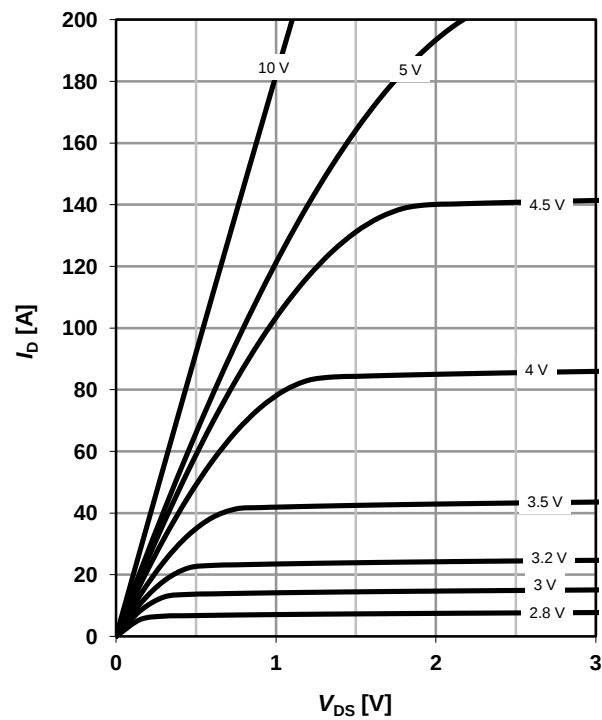
$Z_{thJC}=f(t_p)$

parameter: $D=t_p/T$



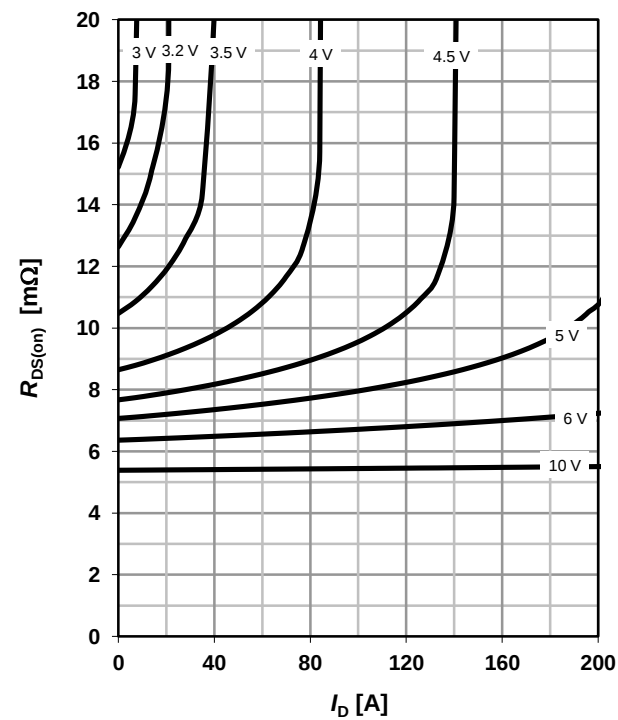
5 Typ. output characteristics

$I_D=f(V_{DS}); T_j=25\text{ }^{\circ}\text{C}$
parameter: V_{GS}



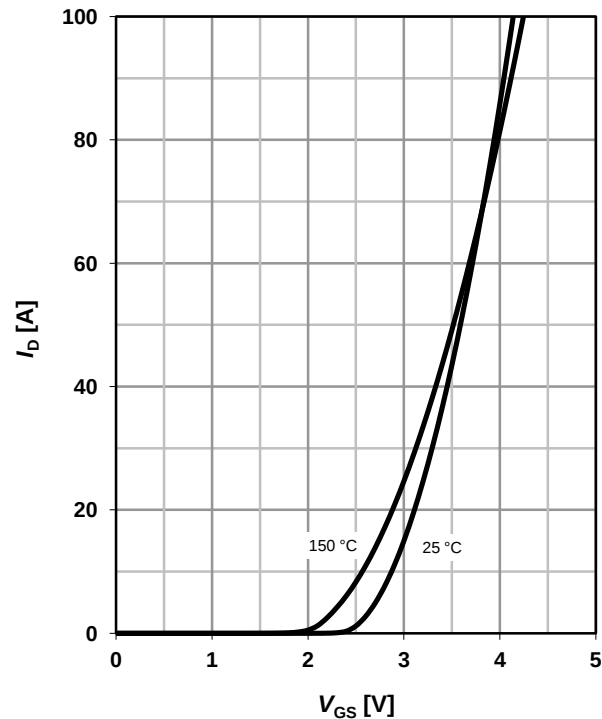
6 Typ. drain-source on resistance

$R_{DS(on)}=f(I_D); T_j=25\text{ }^{\circ}\text{C}$
parameter: V_{GS}



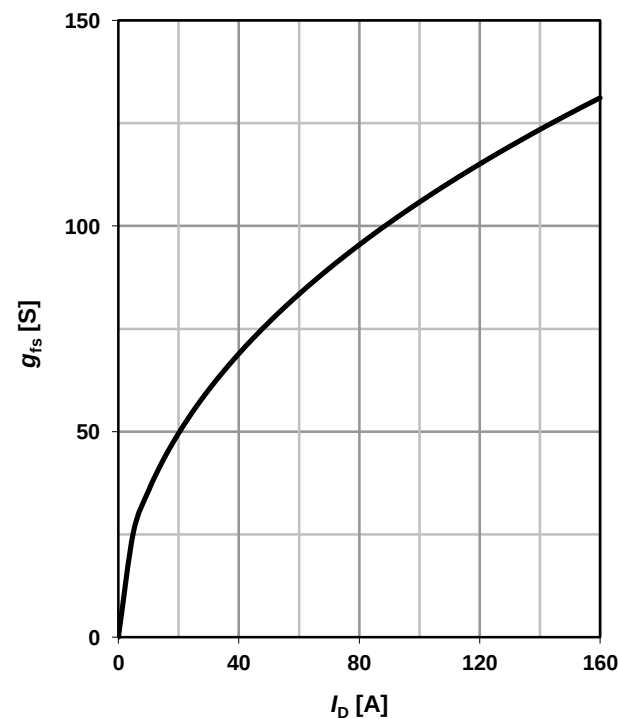
7 Typ. transfer characteristics

$I_D=f(V_{GS}); |V_{DS}|>2|I_D|R_{DS(on)max}$
parameter: T_j



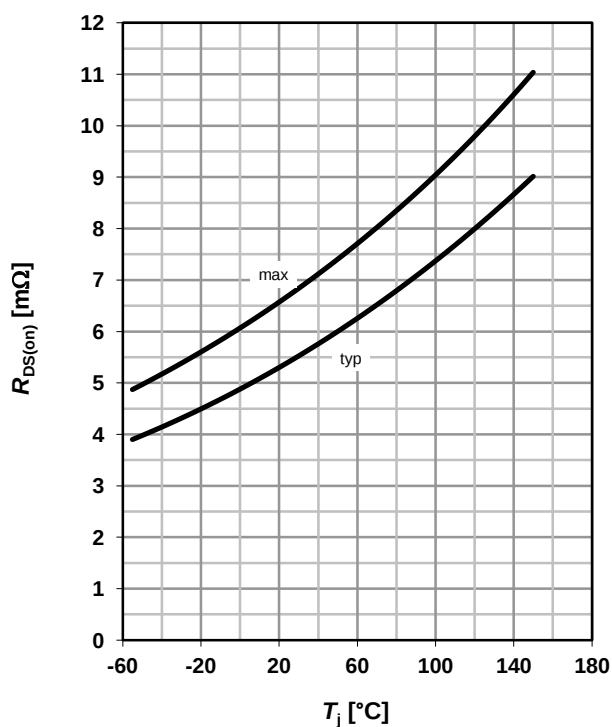
8 Typ. forward transconductance

$g_{fs}=f(I_D); T_j=25\text{ }^{\circ}\text{C}$

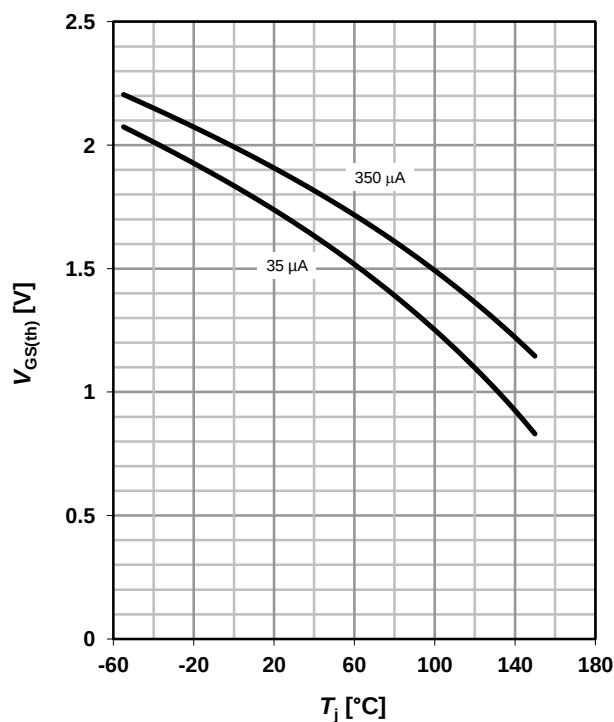


9 Drain-source on-state resistance

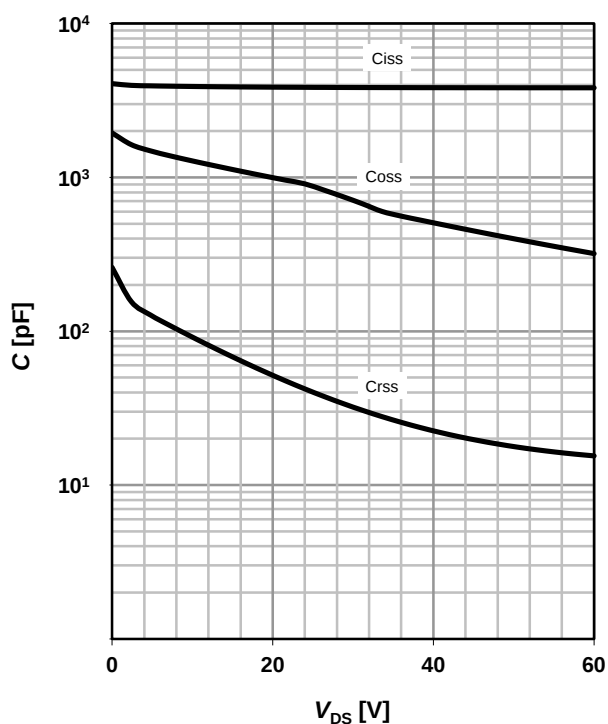
$$R_{DS(on)} = f(T_j); I_D = 50 \text{ A}; V_{GS} = 10 \text{ V}$$

**10 Typ. gate threshold voltage**

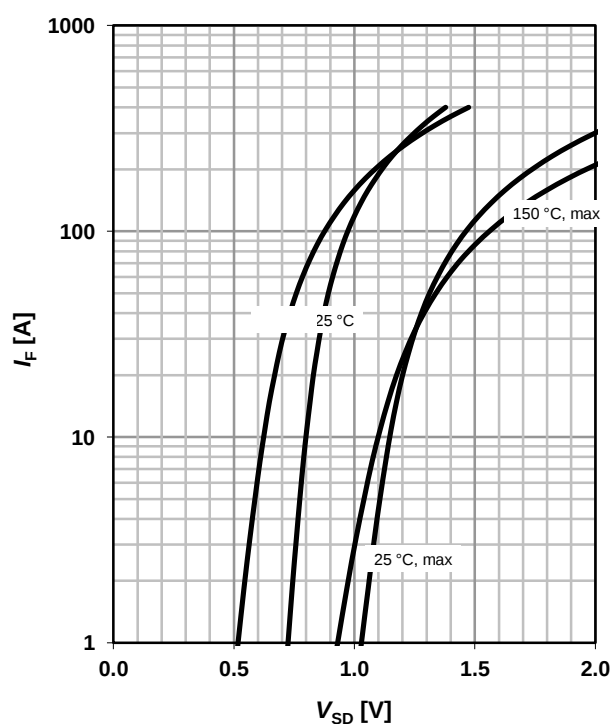
$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}; I_D = 100 \mu\text{A}$$

**11 Typ. capacitances**

$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$

**12 Forward characteristics of reverse diode**

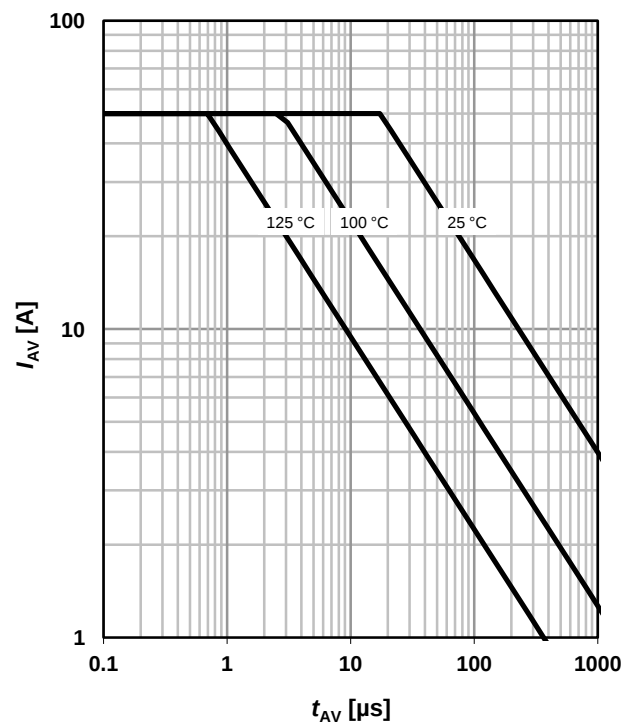
$$I_F = f(V_{SD})$$

parameter: T_j 

13 Avalanche characteristics

$I_{AS}=f(t_{AV}); R_{GS}=25\ \Omega$

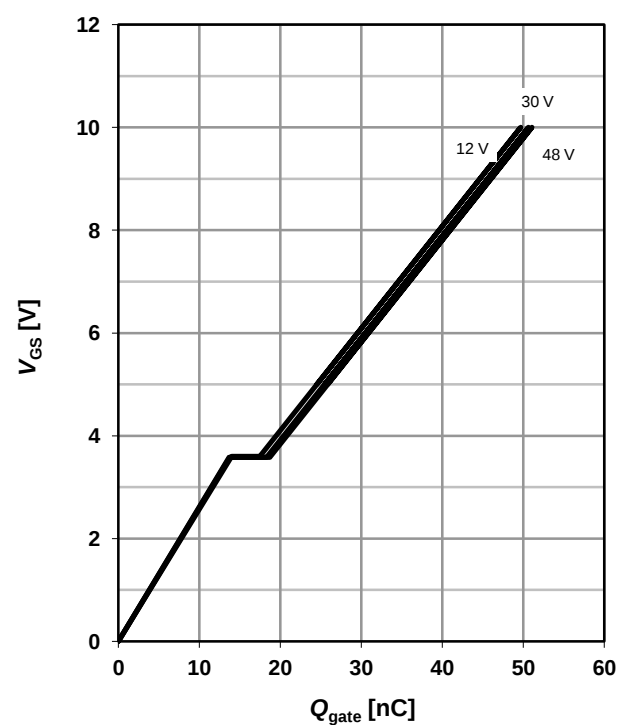
parameter: $T_{j(start)}$



14 Typ. gate charge

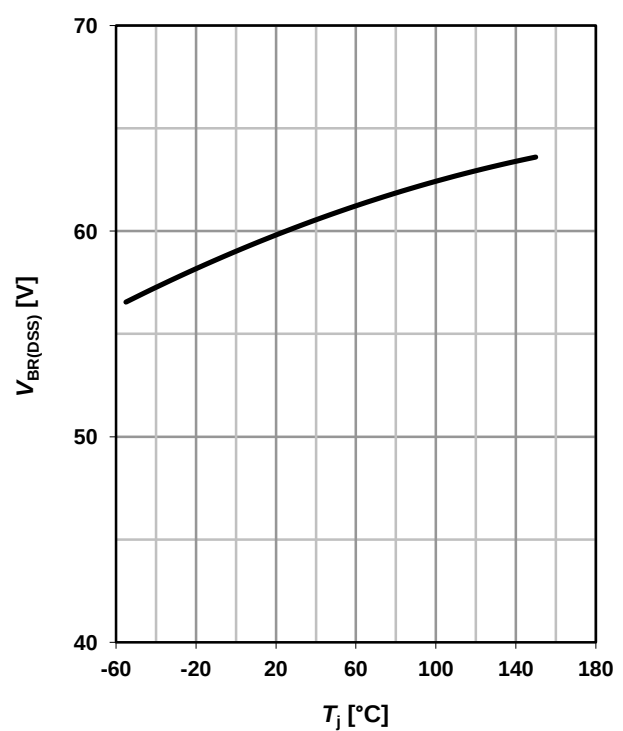
$V_{GS}=f(Q_{gate}); I_D=50\text{ A pulsed}$

parameter: V_{DD}

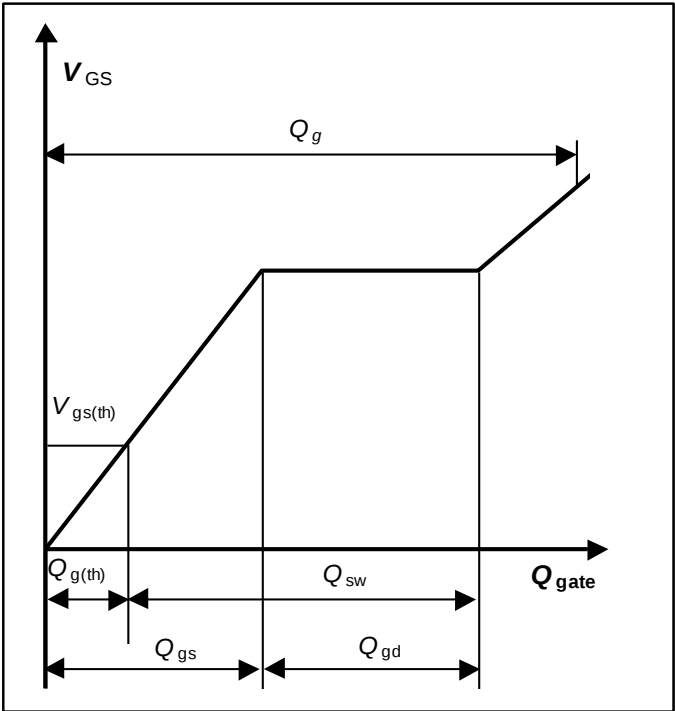


15 Drain-source breakdown voltage

$V_{BR(DSS)}=f(T_j); I_D=1\text{ mA}$

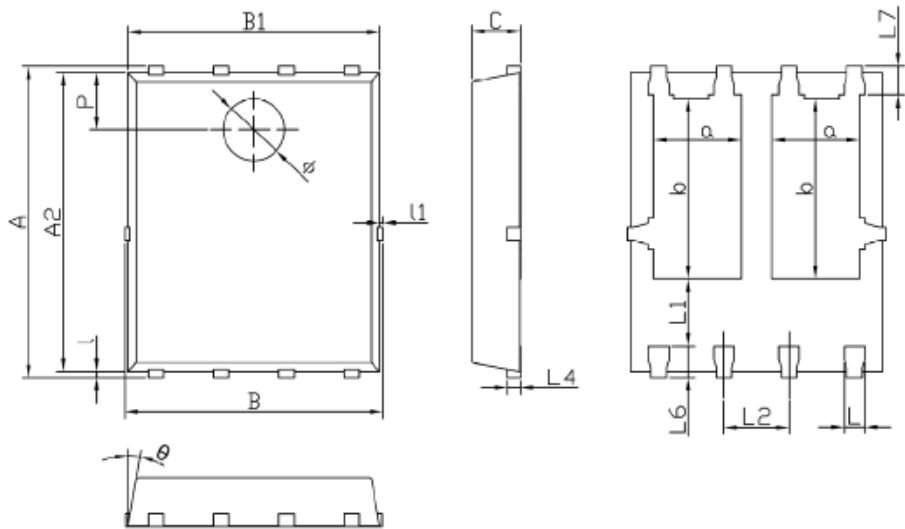


16 Gate charge waveforms



Package Outline

PDFN5x6A-8L Dimensions in mm



Symbol	Dimensions		Symbol	Dimensions	
	Min.	Max.		Min.	Max.
A	5.90	6.10	L1	1.10	-
a	1.605	1.805	l1	-	0.10
A2	5.70	5.80	L2	1.17	1.37
B	4.90	5.10	L4	0.21	0.34
b	3.375	3.575	L6	0.51	0.71
B1	4.80	5.00	L7	0.45	0.65
C	0.90	1.00	P	1.00	1.20
L	0.35	0.45	θ	8°	12°
l	0.06	0.20	Φ	1.10	1.30

Contact Information

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For additional information, please contact your local Sales Representative.

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